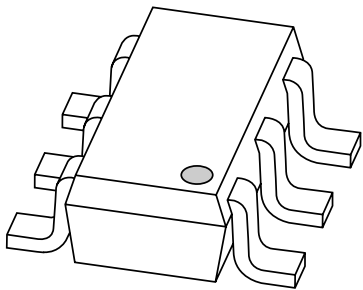


DATA SHEET



PMEM4010ND NPN transistor/Schottky diode module

Product specification

2002 Oct 28

NPN transistor/Schottky diode module

PMEM4010ND

FEATURES

- 600 mW total power dissipation
- High current capability
- Reduces required PCB area
- Reduced pick and place costs
- Small plastic SMD package.

Transistor:

- Low collector-emitter saturation voltage.

Diode:

- Ultra high-speed switching
- Very low forward voltage
- Guard ring protected.

APPLICATIONS

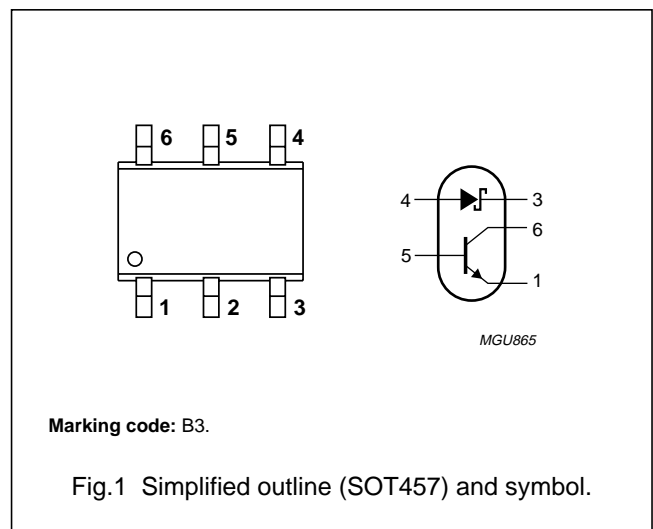
- DC/DC convertors
- Inductive load drivers
- General purpose load drivers
- Reverse polarity protection circuits.

DESCRIPTION

Combination of an NPN transistor with low V_{CEsat} and high current capability and a planar Schottky barrier diode with an integrated guard ring for stress protection in a SOT457 (SC-74) small plastic package.
PNP complement: PMEM4010PD.

PINNING

PIN	DESCRIPTION
1	emitter
2	not connected
3	cathode
4	anode
5	base
6	collector



NPN transistor/Schottky diode module

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
NPN transistor					
V _{CB0}	collector-base voltage	open emitter	–	40	V
V _{CEO}	collector-emitter voltage	open base	–	40	V
V _{EBO}	emitter-base voltage	open collector	–	5	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	2	A
I _{BM}	peak base current		–	1	A
T _j	junction temperature		–	150	°C
Schottky barrier diode					
V _R	continuous reverse voltage		–	20	V
I _F	continuous forward current		–	1	A
I _{FSM}	non repetitive peak forward current	t = 8.3 ms half sinewave; JEDEC method	–	5	A
T _j	junction temperature		–	125	°C
Combined device					
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	–	600	mW
T _{stg}	storage temperature		–65	+150	°C
T _{amb}	operating ambient temperature		–65	+125	°C

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	208	K/W

Note

1. Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1 cm².

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CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

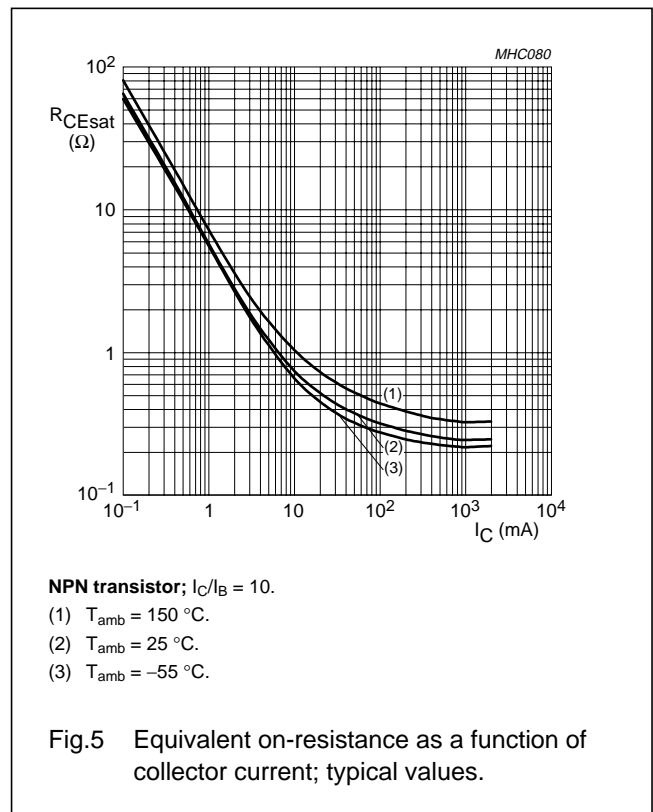
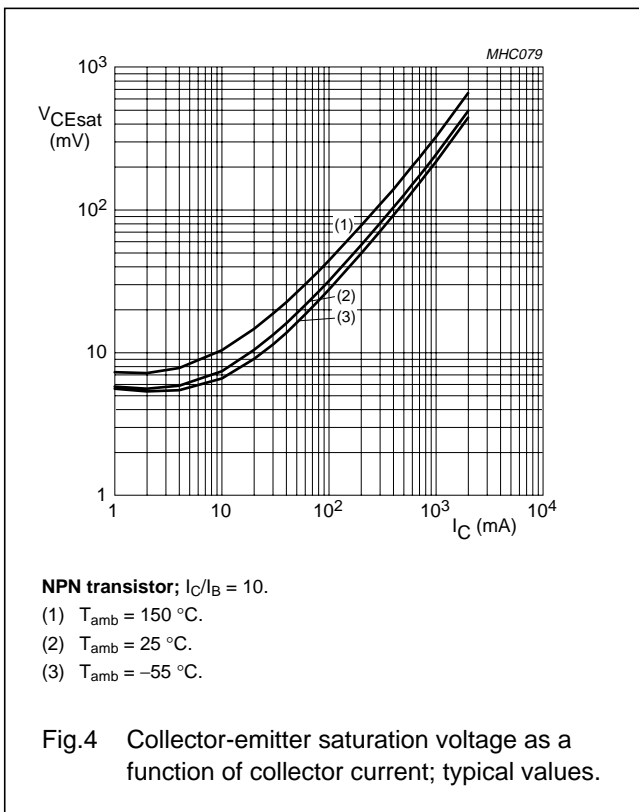
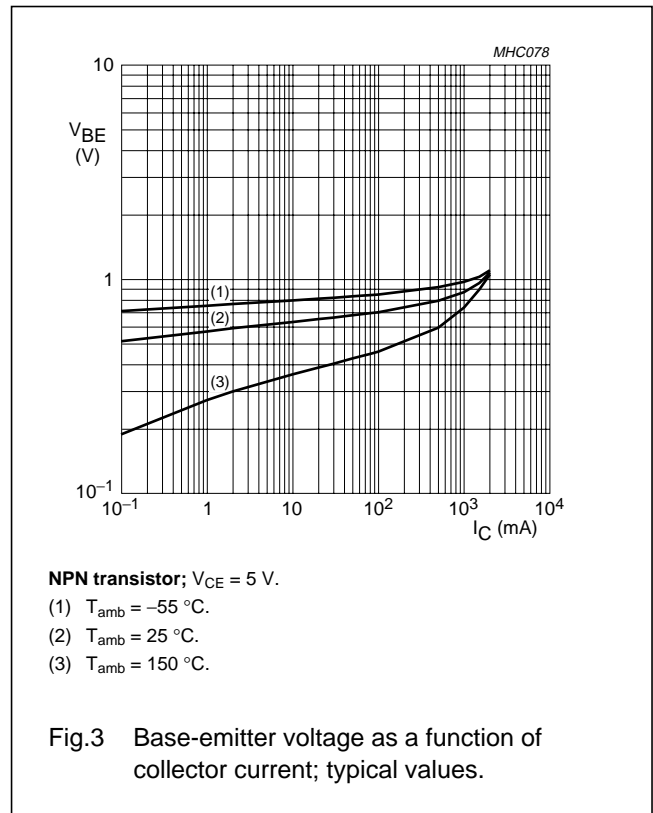
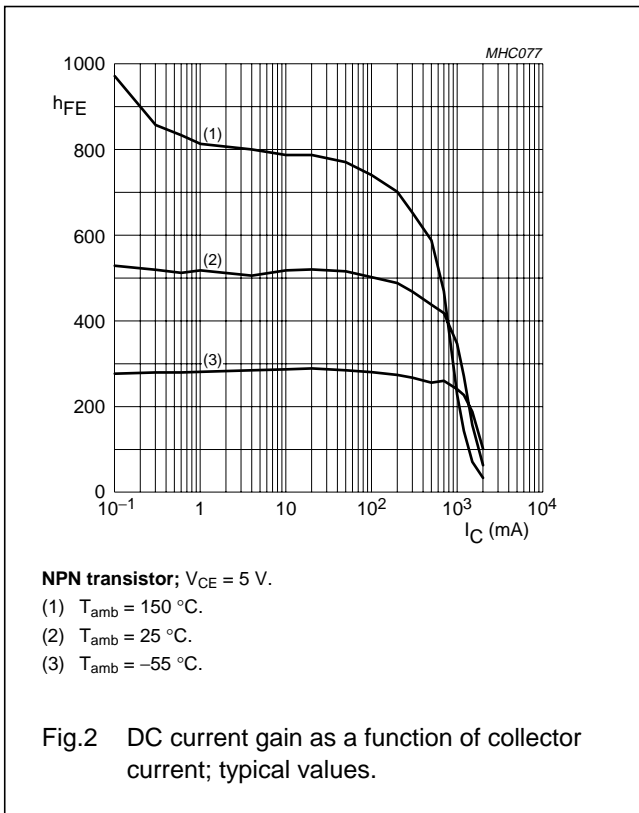
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
NPN transistor						
I_{CBO}	collector-base cut-off current	$V_{CB} = 40\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 40\text{ V}; I_E = 0; T_{amb} = 150\text{ °C}$	–	–	50	μA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0$	–	–	100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	300	–	–	
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	300	–	900	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	200	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	–	–	80	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	–	110	mV
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	190	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	–	–	1.2	V
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	260	<220	m Ω
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	–	–	1.1	V
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V};$ $f = 100\text{ MHz}$	150	–	–	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	–	10	pF
Schottky barrier diode						
V_F	continuous forward voltage	$I_F = 10\text{ mA}; \text{note 1}$	–	240	270	mV
		$I_F = 100\text{ mA}; \text{note 1}$	–	300	350	mV
		$I_F = 1000\text{ mA}; \text{see Fig.7; note 1}$	–	480	550	mV
I_R	reverse current	$V_R = 5\text{ V}; \text{note 1}$	–	5	10	μA
		$V_R = 8\text{ V}; \text{note 1}$	–	7	20	μA
		$V_R = 15\text{ V}; \text{see Fig.8; note 1}$	–	10	50	μA
C_d	diode capacitance	$V_R = 5\text{ V}; f = 1\text{ MHz}; \text{see Fig.9}$	–	19	25	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.

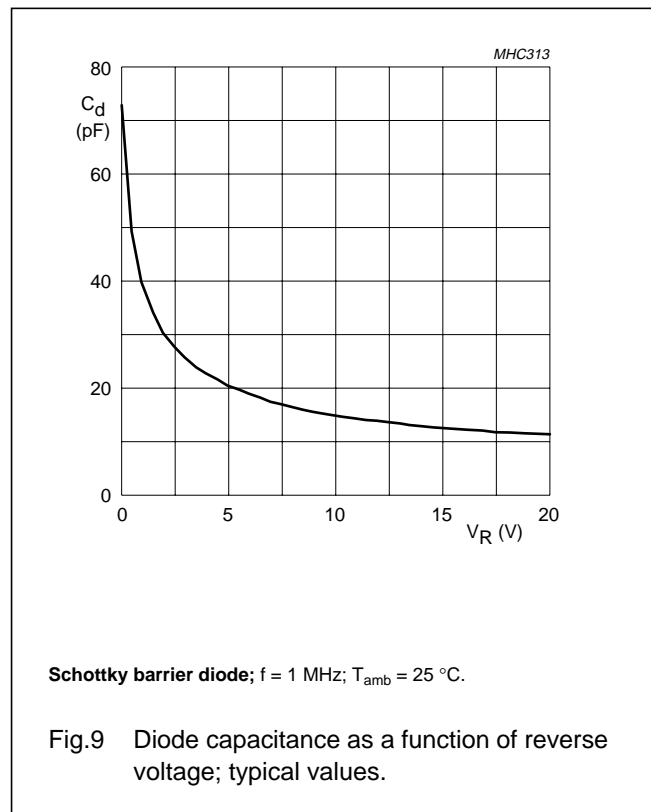
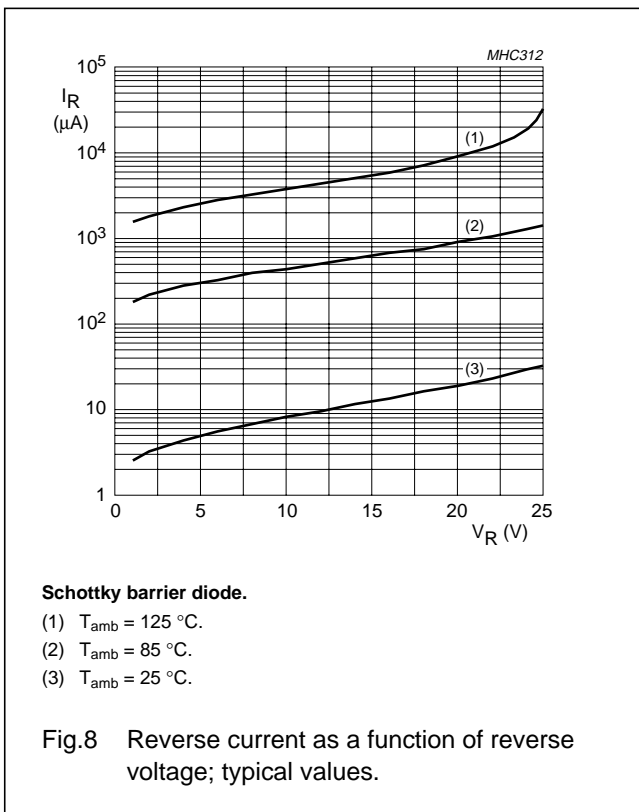
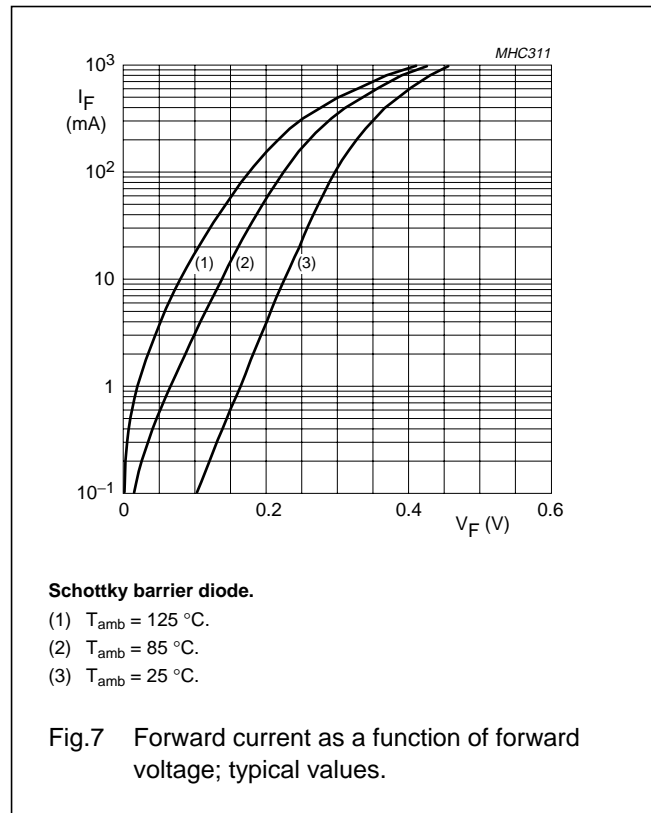
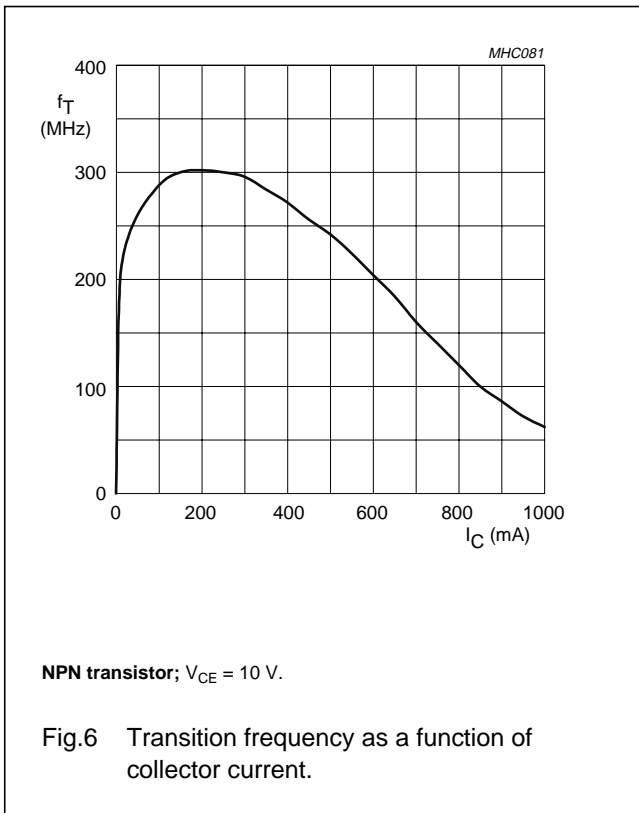
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NPN transistor/Schottky diode module

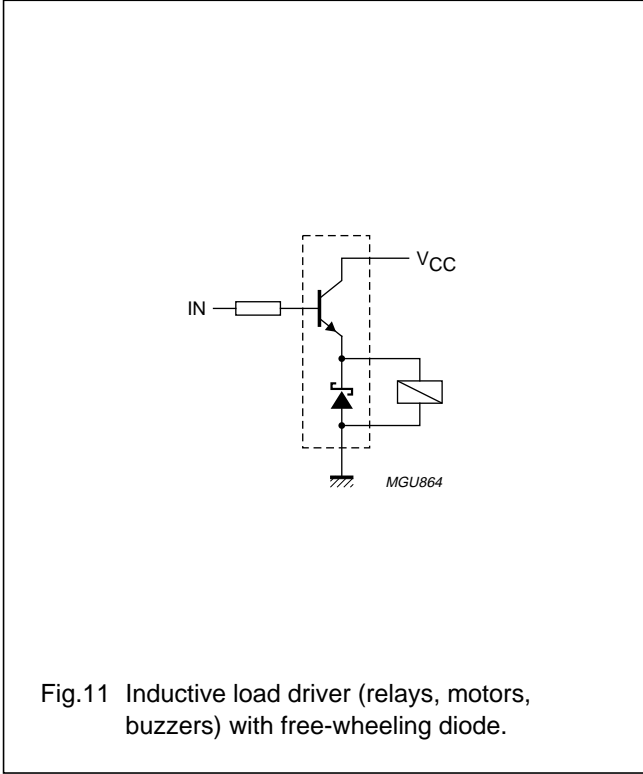
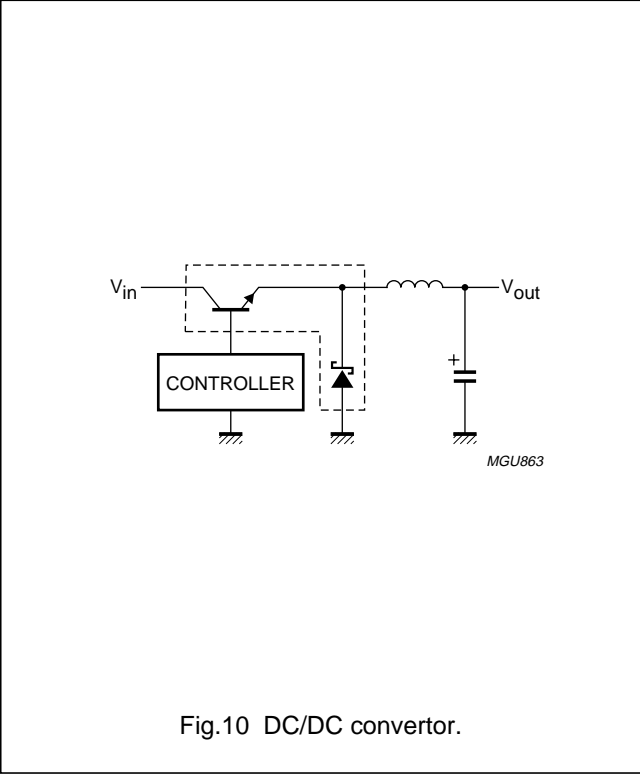
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NPN transistor/Schottky diode module

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APPLICATION INFORMATION



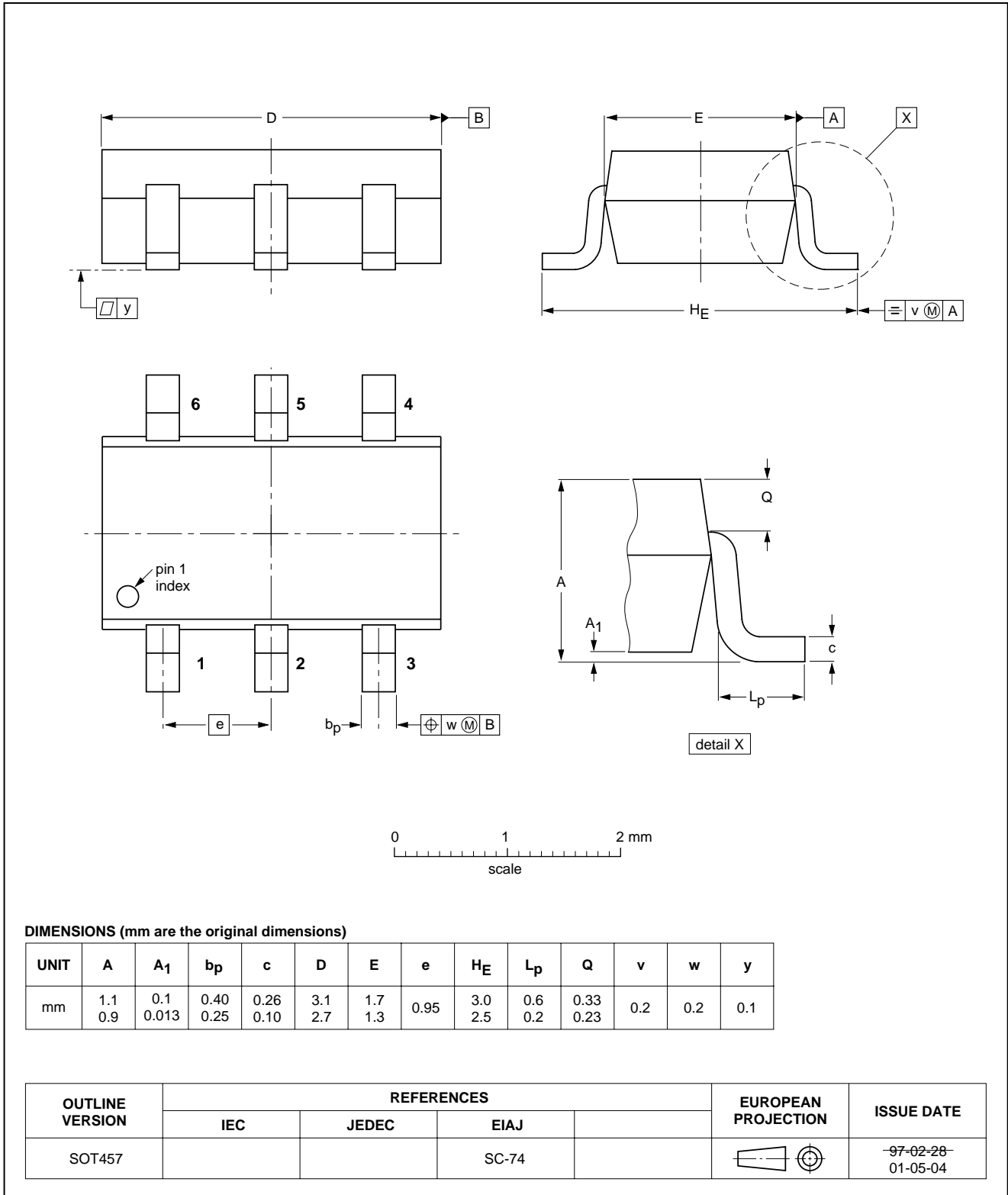
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT457



NPN transistor/Schottky diode module

PMEM4010ND

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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NOTES

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NOTES

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